

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
21 July 2005 (21.07.2005)

PCT

(10) International Publication Number
WO 2005/067035 A1

(51) International Patent Classification⁷: **H01L 21/8242**

(21) International Application Number:

PCT/US2003/038559

(22) International Filing Date: 4 December 2003 (04.12.2003)

(25) Filing Language:

English

(26) Publication Language:

English

(71) Applicant (*for all designated States except US*): **INTERNATIONAL BUSINESS MACHINES CORPORATION** [US/US]; New Orchard Road, Armonk, NJ 10504 (US).

(72) Inventors; and

(75) Inventors/Applicants (*for US only*): **DOKUMACI, Omer, H.** [TR/US]; 32E Wintrop Court, Wappingers Falls, NY 12590 (US). **RONSHHEIM, Paul** [US/US]; 118 Hollyberry Drive, Hopewell Junction, NY 12533 (US).

(74) Agent: **PEPPER, Margaret, A.**; International Business Machines Corporation, 2070 Route 53, Hopewell Junction, NY 12533 (US).

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (*regional*): ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— *of inventorship (Rule 4.17(iv)) for US only*

Published:

— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD FOR FORMING NON-AMORPHOUS, ULTRA-THIN SEMICONDUCTOR DEVICES USING SACRIFICIAL IMPLANTATION LAYER

(57) Abstract: A method for forming a semiconductor device includes defining a sacrificial layer (108) over a single crystalline substrate (106). The sacrificial layer (108) is implanted with a dopant species in a manner that prevents the single crystalline substrate (106) from becoming substantially amorphized. The sacrificial layer (108) is annealed so as to drive said dopant species from said sacrificial layer (108) into said single crystalline substrate (106).



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